a single team databook with tightly controlled structure

Main Body

- Title Page
- Contents including list of all cells with page numbers
- Introduction (max 3 sides)
- Datasheet (1 per cell 1 side each)
- Summary of results (max 1 side)

Appendix A

- Team Management (max 1 side)
- Division of Labour Form (1 side)

Appendix B

• Design detail for major cells (max 2 sides per major cell)

• Title Page

Cell Library Databook

by Team C1

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• Introduction (max 3 sides)

Introduces the library and the databook.

Gives detail of features common to all cells in the library (e.g. cell height)

Picture showing position of signals and other cell structures such as the N-well as they exist at the interface between cells

• Datasheet (1 side per cell¹)

Include datasheets for cells to be used by the ASIC designer (e.g. scanreg) rather than cells only used by library cell designers (e.g. rdtype, smux3).

- cell name
- cell description
- cell designer(s)
- symbol²
- gate level circuit diagram³
- abstract
 - black box view showing dimensions
- table of measured parameters
- verilog simulation waveform

³no gate level circuit diagram required for nand, nor, inv, tiehigh, tielow, rowcrosser

¹trivial support cells may be combined on one page

²no symbol exists for leftbuf, rightend, tiehigh, tielow, rowcrosser

• Design detail for major cells (max 2 sides per major cell)

rdtype, smux2, smux3, fulladder, halfadder, xor2, leftbuf A sub-section should exist for each designer, dealing with the major cells they have designed.

For each cell the following information should be included in the design detail:⁴

- transistor level circuit diagram
 with comments on derivation if appropriate
- stick diagram
- details of circuit for loaded simulation
- results of loaded simulation numerical and graphical

⁴take care with diagrams, don't scan/capture my schematics, avoid screen capture of simulation and layout if possible, and avoid using inappropriate pre-defined circuit symbols (e.g. MOS transistors with visible substrate connection).

• Presentation

- Use full sentences and paragraphs
 note form is acceptable on the datasheets but not in design detail sections or elsewhere in the databook
- Cover

The handin system allows you to print a standard cover for this report

– Binding

This report must be bound. If printing double sided, then a neat line of staples down the long edge of the report will be sufficient.

Documentation for this exercise should be submitted to the school office.

Deadline for documentation is 16:00 on Tuesday 11th December.

Final note: extra credit may be given for advanced characterization e.g. Δt_p , t_{setup} (for sequential gates), or clock skew simulations (for left end of row cell)